

Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
4.5 to 20	0.105 @ $V_{IN} = 10$ V	± 2.3
	0.150 @ $V_{IN} = 5.0$ V	± 1.9
	0.175 @ $V_{IN} = 4.5$ V	± 1.7



ESD Protected
3000 V
4.5-V Rated

FEATURES

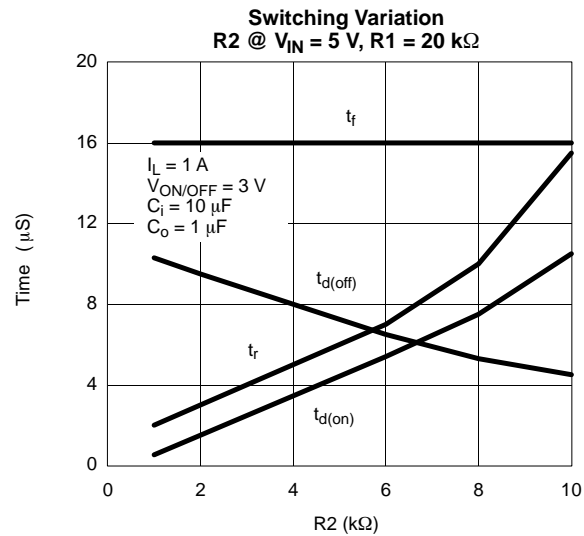
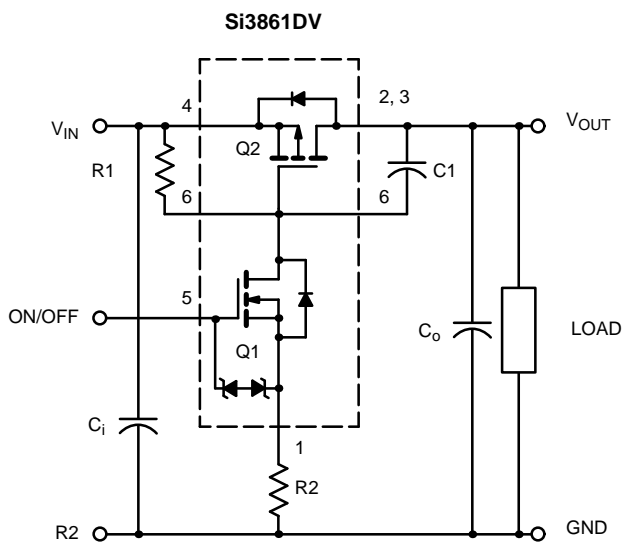
- 105-m Ω Low $r_{DS(on)}$ TrenchFET™
- 4.5 to 20-V Input
- 1.5 to 8 -V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000-V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate

DESCRIPTION

The Si3861DV includes a p- and n-channel MOSFET in a single TSOP-6 package. The low on-resistance p-channel TrenchFET® is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a

level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5-V. The Si3861DV operates on supply lines from 4.5 to 20-V, and can drive loads up to 2.3 A.

APPLICATION CIRCUITS



Note: For R2 switching variations with other $V_{IN}/R1$ combinations See Typical Characteristics

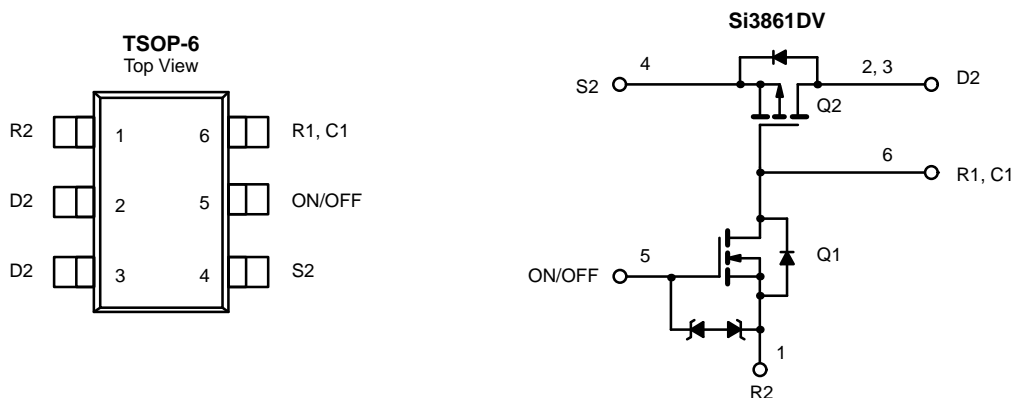
COMPONENTS

R1	Pull-Up Resistor	Typical 10 k Ω to 1 m Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

*Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

The Si3861DV is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Input Voltage		V _{IN}	20	V
ON/OFF Voltage		V _{ON/OFF}	8	
Load Current	Continuous ^{a, b}	I _L	± 2.3	A
	Pulsed ^{b, c}		± 4	
Continuous Intrinsic Diode Conduction ^a		I _S	-1	
Maximum Power Dissipation ^a		P _D	0.83	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)		ESD	3	kV

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R _{thJA}	120	150	°C/W
Maximum Junction-to-Foot (Q2)	R _{thJC}	35	50	

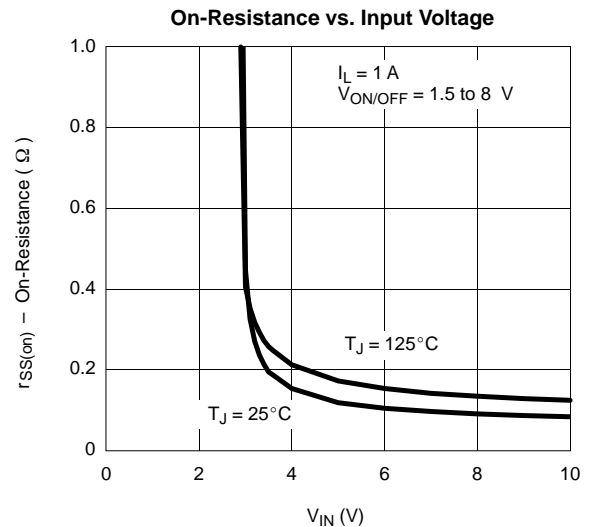
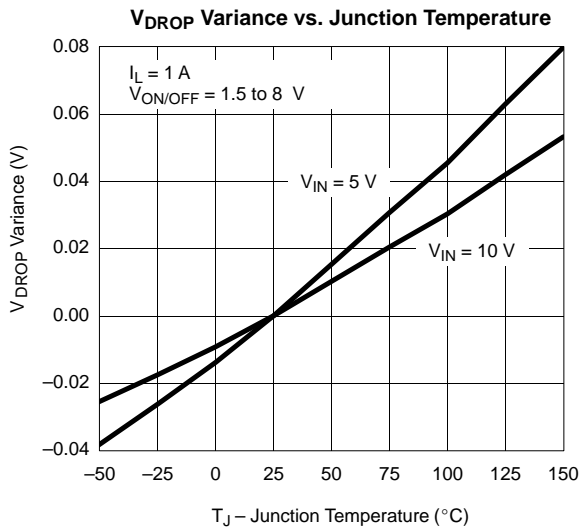
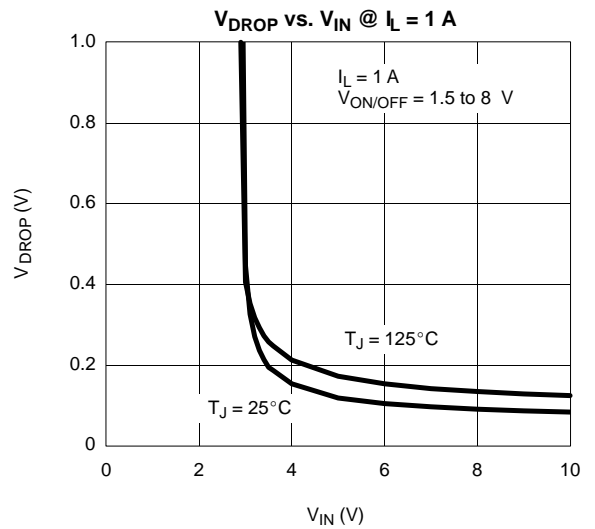
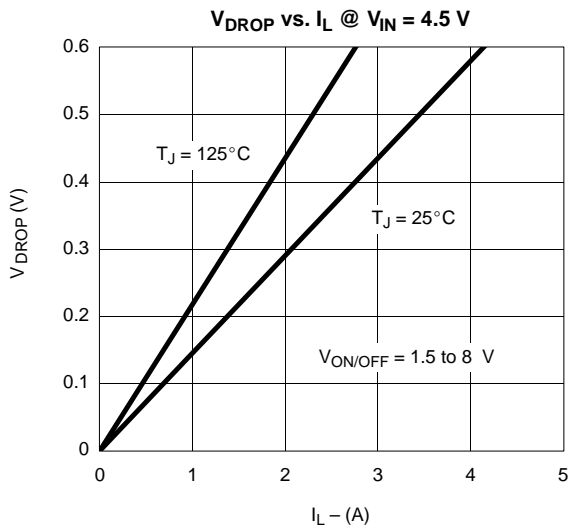
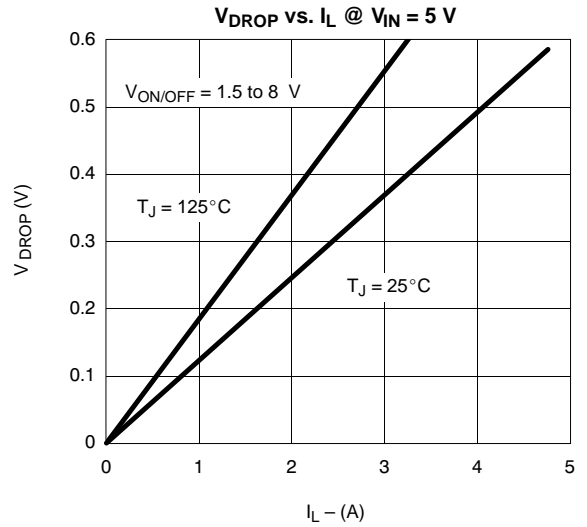
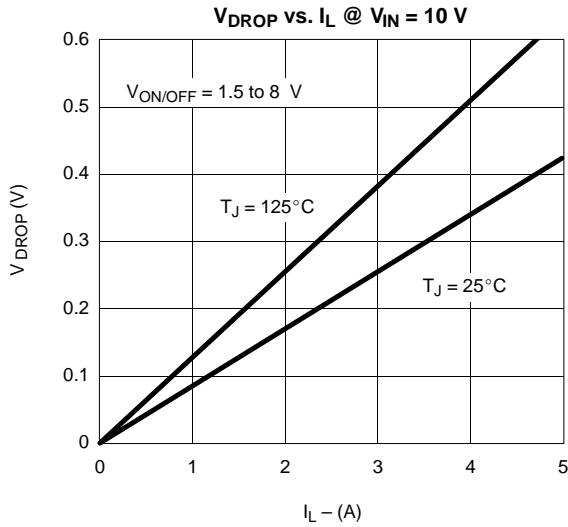
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
OFF Characteristics							
Reverse Leakage Current	I _{FL}	V _{IN} = 30 V, V _{ON/OFF} = 0 V			1	μA	
Diode Forward Voltage	V _{SD}	I _S = -1 A		-0.8	-1	V	
ON Characteristics							
Input Voltage Range	V _{IN}		4.5		20	V	
On-Resistance (p-channel) @ 1 A	r _{DS(on)}	V _{ON/OFF} = 1.5 V I _D = 1 A	V _{IN} = 10 V		0.085	0.105	Ω
			V _{IN} = 5.0 V		0.123	0.150	
			V _{IN} = 4.5 V		0.145	0.175	
On-State (p-channel) Drain-Current	I _{D(on)}	V _{IN-OUT} ≤ 0.2 V, V _{IN} = 10 V, V _{ON/OFF} = 1.5 V	1			A	
		V _{IN-OUT} ≤ 0.3 V, V _{IN} = 5 V, V _{ON/OFF} = 1.5 V	1				

Notes

- a. Surface Mounted on FR4 Board.
- b. V_{IN} = 12, V_{ON/OFF} = 8 V, T_A = 25 °C.
- c. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2%.



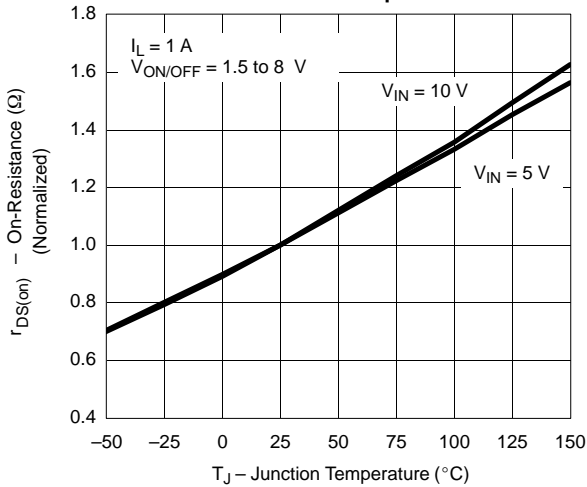
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



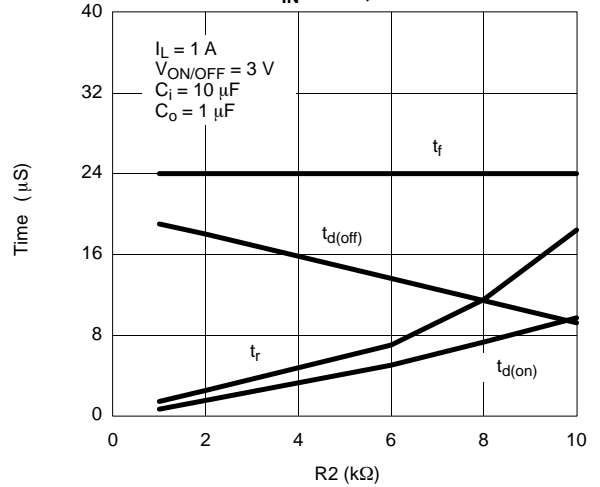


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

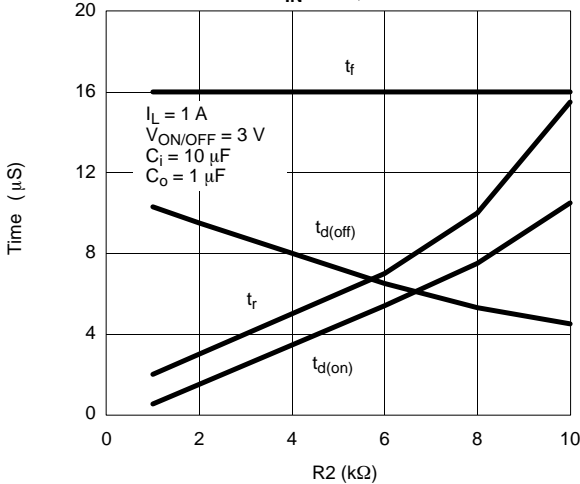
Normalized On-Resistance vs. Junction Temperature



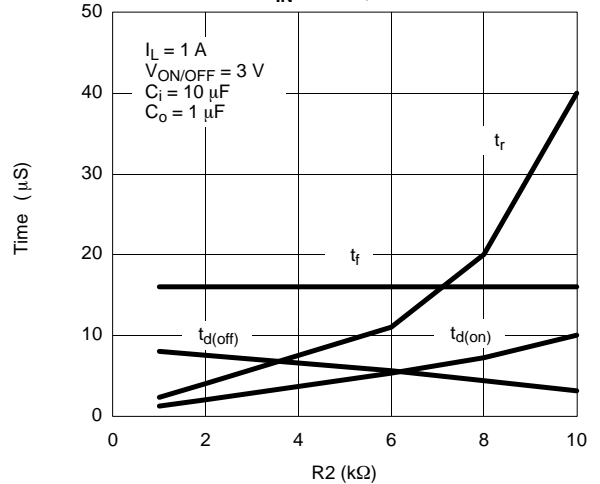
Switching Variation R2 @ V_IN = 10 V, R1 = 20 kΩ



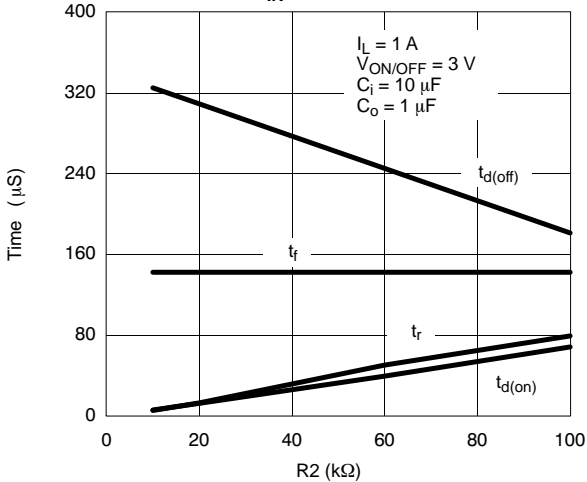
Switching Variation R2 @ V_IN = 5 V, R1 = 20 kΩ



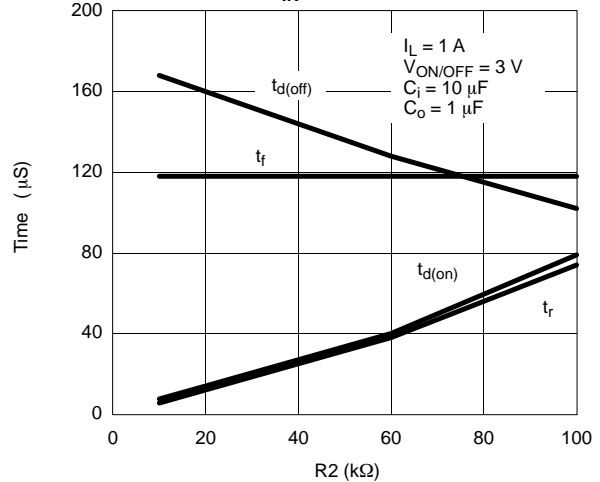
Switching Variation R2 @ V_IN = 4.5 V, R1 = 20 kΩ



Switching Variation R2 @ V_IN = 10 V, R1 = 300 kΩ



Switching Variation R2 @ V_IN = 5 V, R1 = 300 kΩ





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

